

DMG3401LSN

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on) max}$	I_D $T_A = 25^\circ C$
-30V	50mΩ @ $V_{GS} = -10V$	-3.7A
	60mΩ @ $V_{GS} = -4.5V$	-3.3A
	85mΩ @ $V_{GS} = -2.5V$	-2.7A

Description

This new generation Small-Signal enhancement mode MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

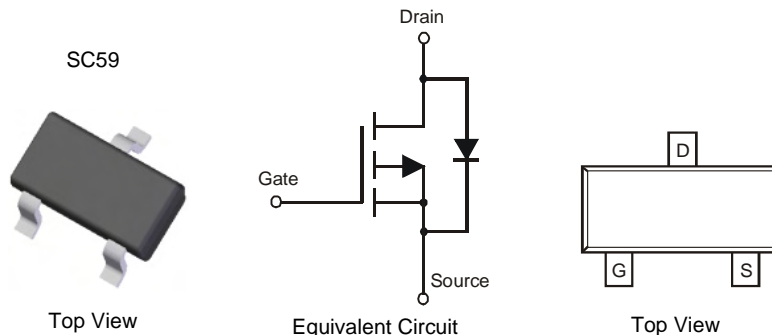
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

Features

- Low Input Capacitance
- Low On-Resistance
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SC59
- Case Material: Molded Plastic "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

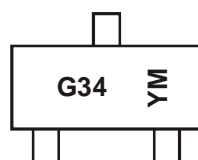


Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3401LSN-7	SC59	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

Marking Information



G34 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: Y = 2011)
 M = Month (ex: 9 = September)

Date Code Key

Year	2011	2012	2013	2014	2015	2016	2017
Code	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 5) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	-3.0	A
		$T_A = +70^\circ\text{C}$		-2.3	
Continuous Drain Current (Note 6) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	-3.7	A
		$T_A = +70^\circ\text{C}$		-2.9	
Pulsed Drain Current (10 μs pulse, duty cycle = 1%)			I_{DM}	-30	A
Maximum Body Diode Continuous Current (Note 6)			I_S	-1.5	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation	(Note 5)	P_D	0.8	W
	(Note 6)		1.2	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	159	$^\circ\text{C/W}$
	(Note 6)		105	
Thermal Resistance, Junction to Case	(Note 6)	$R_{\theta JC}$	36	$^\circ\text{C}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = 25^\circ\text{C}$	I_{DSS}	-	-	-1.0	μA	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Body Leakage	I_{GSS}	-	-	± 100	nA	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.5	-1.0	-1.3	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	-	41	50	m Ω	$V_{GS} = -10\text{V}, I_D = -4\text{A}$
		-	47	60		$V_{GS} = -4.5\text{V}, I_D = -3.5\text{A}$
		-	60	85		$V_{GS} = -2.5\text{V}, I_D = -2.5\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	-	12	-	S	$V_{DS} = -5\text{V}, I_D = -4\text{A}$
Diode Forward Voltage	V_{SD}	-	-0.8	-1.0	V	$V_{GS} = 0\text{V}, I_S = -1\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	1326	-	pF	$V_{DS} = -15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	-	103	-		
Reverse Transfer Capacitance	C_{rss}	-	71	-		
Gate Resistance	R_g	-	7.3	-	Ω	$V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Total Gate Charge ($V_{GS} = -4.5\text{V}$)	Q_g	-	11.6	-	nC	$V_{DD} = -15\text{V}, I_D = -4\text{A}$
Total Gate Charge ($V_{GS} = -10\text{V}$)	Q_g	-	25.1	-		
Gate-Source Charge	Q_{gs}	-	2	-		
Gate-Drain Charge	Q_{gd}	-	1.7	-		
Turn-On Delay Time	$t_{D(on)}$	-	8	-	nS	$V_{DS} = -15\text{V}, V_{GS} = -10\text{V}, R_{GEN} = 6\Omega, R_L = 3.75\Omega$
Turn-On Rise Time	t_r	-	13	-		
Turn-Off Delay Time	$t_{D(off)}$	-	71	-		
Turn-Off Fall Time	t_f	-	38	-		

- Notes:
3. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 4. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
 5. Short duration pulse test used to minimize self-heating effect.
 6. Guaranteed by design. Not subject to production testing